

## Silicon Super Fast Recovery Diode

 $V_{RRM} = 50\text{ V} - 600\text{ V}$ 
 $I_F = 70\text{ A}$ 

### Features

- High Surge Capability
- Types up to 600 V  $V_{RRM}$

**D61-3M Package**


### Maximum ratings, at $T_j = 25\text{ °C}$ , unless otherwise specified ("R" devices have leads reversed)

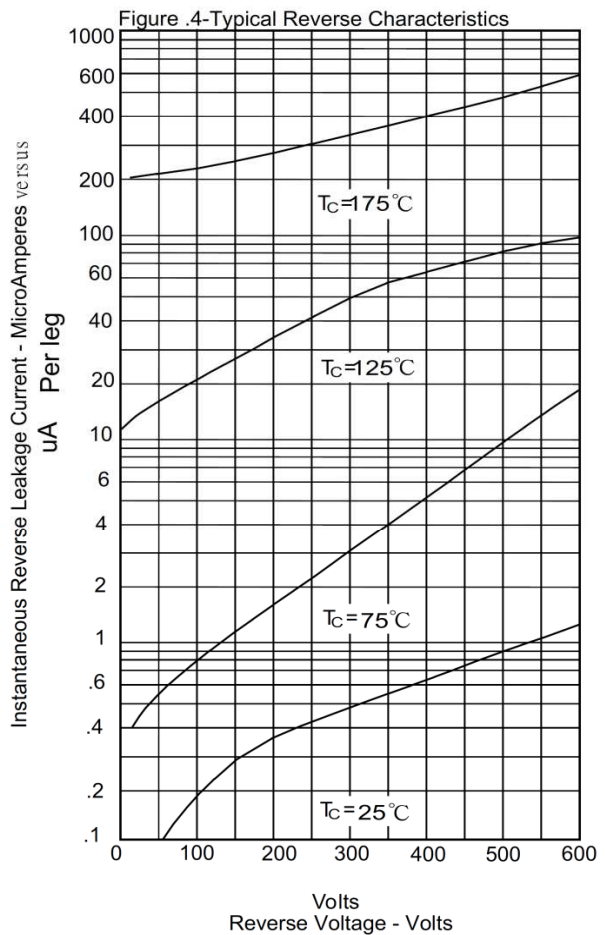
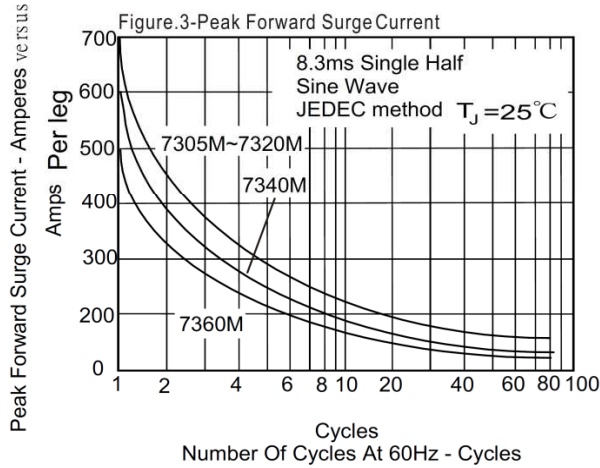
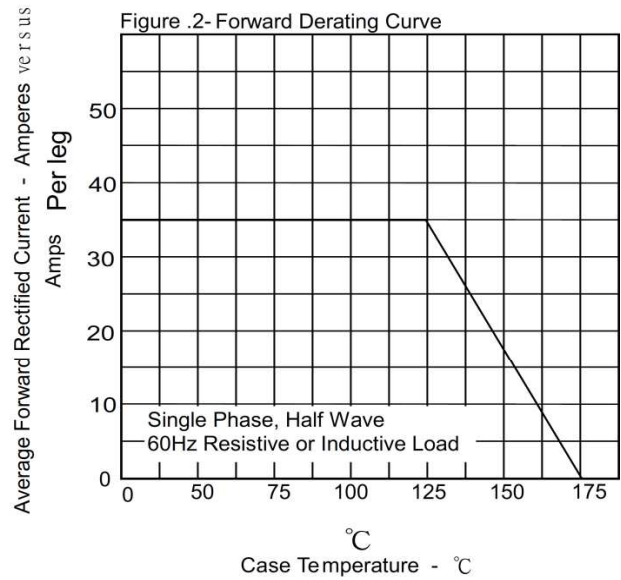
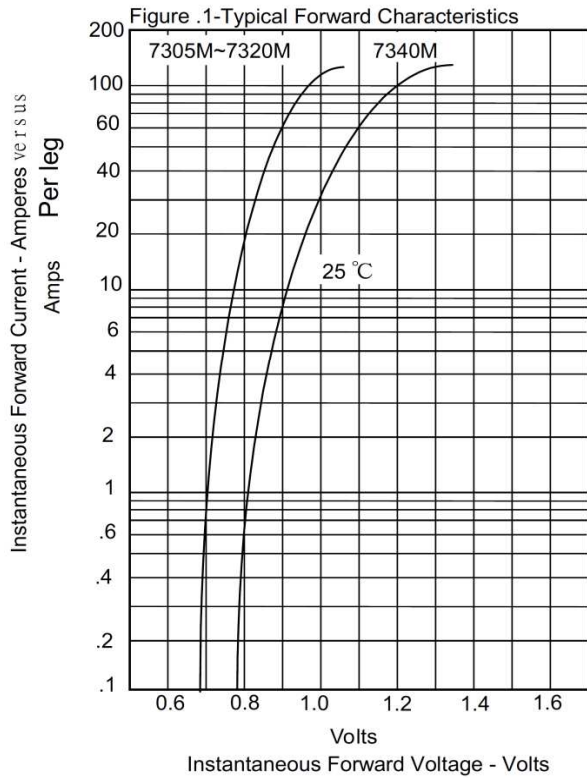
Parameter	Symbol	Conditions	UFT7340M	UFT7360M	Unit
Repetitive peak reverse voltage	$V_{RRM}$		400	600	V
RMS reverse voltage	$V_{RMS}$		280	420	V
DC blocking voltage	$V_{DC}$		400	600	V
Continuous forward current	$I_F$	$T_C \leq 125\text{ °C}$	70	70	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$ , $t_p = 8.3\text{ ms}$	600	500	A
Operating temperature	$T_j$		-65 to 175	-65 to 175	°C
Storage temperature	$T_{stg}$		-65 to 175	-65 to 175	°C

### Electrical characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	UFT7340M	UFT7360M	Unit
Diode forward voltage	$V_F$	$I_F = 35\text{ A}$ , $T_j = 25\text{ °C}$	1.3	1.7	V
Reverse current	$I_R$	$V_R = 50\text{ V}$ , $T_j = 25\text{ °C}$	25	25	$\mu\text{A}$
		$V_R = 50\text{ V}$ , $T_j = 125\text{ °C}$	3	3	mA

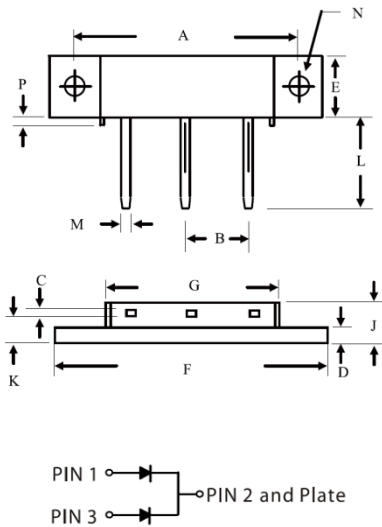
### Recovery Time

Maximum reverse recovery time	$T_{RR}$	$I_F = 0.5\text{ A}$ , $I_R = 1.0\text{ A}$ , $I_{RR} = 0.25\text{ A}$	75	90	nS
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## Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



DIM	Inches		Millimeters	
	Min	Max	Min	Max
A	1.180	1.195	29.97	30.35
B	0.200	NOM	5.08	NOM
C	0.027	0.037	0.69	0.94
D	0.088	0.098	2.24	2.49
E	0.350	0.370	8.89	9.40
F	1.490	1.510	37.85	38.35
G	0.695	0.715	17.65	18.16
J	0.240	0.260	6.10	6.60
K	0.115	0.135	2.92	3.43
L	0.457	0.477	11.61	12.12
M	0.065	0.085	1.65	2.16
N	0.151	0.161	3.84	4.09
P	0.015	0.025	0.38	0.64